Silicon NPN Power Transistors 2SC2902

DESCRIPTION

- With TO-3 package
- High voltage ,high speed

APPLICATIONS

- Converters
- Inverters
- Switching regulators
- Motor controls

Fig.1 simplified outline (TO-3) and symbol

PINNING (See Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	CONDITIONS	MAX	UNIT
V_{CBO}	Collector-base voltage	Open emitter	800	V
V_{CEO}	Collector-emitter voltage	Open base	400	V
V_{EBO}	Emitter-base voltage	Open collector	9	V
I_C	Collector current		15	A
I_{CM}	Collector current-Peak		30	A
P_C	Collector power dissipation	T_C=25℃	150	W
T_j	Junction temperature		200	℃
T_{stg}	Storage temperature		-65~200	℃

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CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-emitter sustaining voltage	I_C=0.1A ; I_B=0; L=25mH	400			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	I_E=1mA; I_C=0	9			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=7.5A; I_B=2.5A			1.0	V
V_{BEsat}	Base-emitter saturation voltage	I_C=7.5A; I_B=2.5A			1.5	V
I_{CBO}	Collector cut-off current	V_{CB}=640V; I_E=0			50	μA
I_{EBO}	Emitter cut-off current	V_{EB}=9V; I_C=0			50	μA
h_{FE}	DC current gain	I_C=7.5A ; V_{CE}=5V	10		35	

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PACKAGE OUTLINE

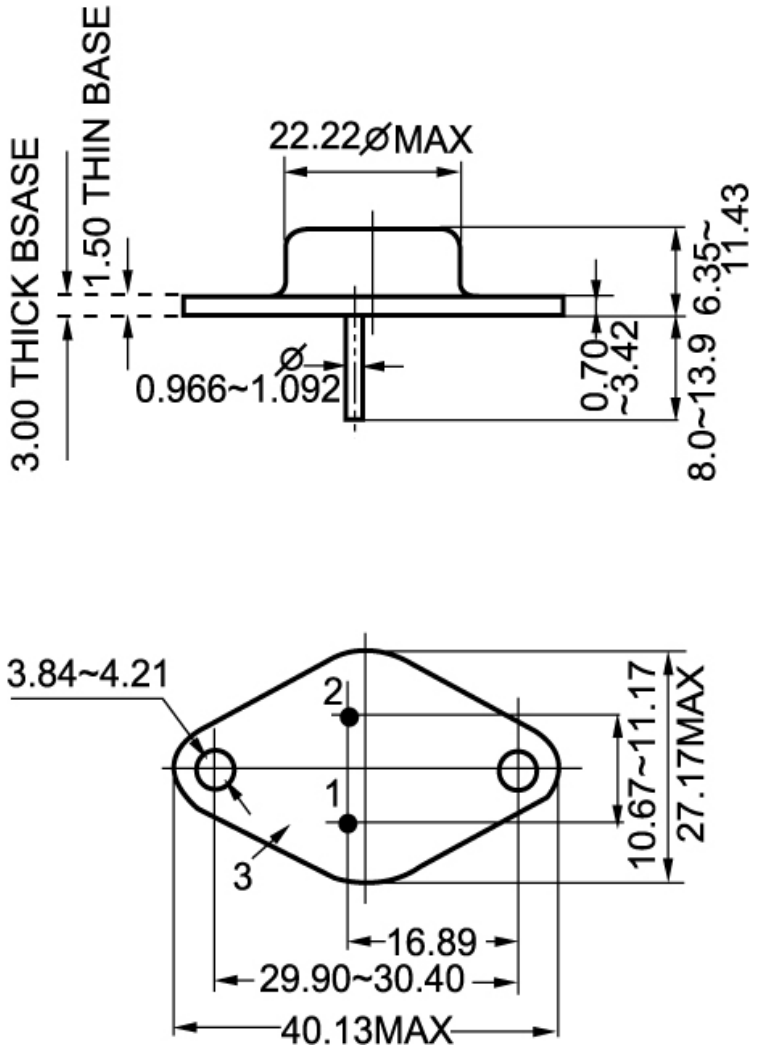

Fig.2 Outline dimensions